

ABSTRACT OF THE DISCLOSURE

The invention relates to a method of producing a thin layer of semiconductor material including :——

5 — - a step of implanting ions through a flat face (2) of a semiconductor wafer in order to create a layer of microcavities, the ion dose being within a specific range in order to avoid the formation of blisters on the flat face, —————

— - a thermal treatment step in order to achieve coalescence of the microcavities —————

10 — - possibly, a step of creating at least one electronic component (5) in the thin layer (6), ———

— - a separation step of separating the thin layer (6) from the rest (7) of the wafer.

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~~FIG. 4~~